

AMENDMENTS TO THE CLAIMS

1-11 (Cancelled).

12. (New) A method for driving a nonvolatile memory, the nonvolatile memory comprising:

a transistor having a source region, a drain region and a floating gate electrode;

a dielectric capacitor, which is connected to the floating gate electrode and has a dielectric layer;

a ferroelectric capacitor, which is connected to the floating gate electrode and has a ferroelectric layer;

first and second polarization voltage application terminals, which are connected to the dielectric capacitor and the ferroelectric capacitor, respectively, and which apply voltage for generating polarization to the ferroelectric capacitor; and

a ground terminal and a power source voltage terminal connected to the source region and the drain region, respectively,

wherein during writing, in accordance with the information "0" or "1" that is to be written, the voltage applied to the first and second polarization voltage application terminals is reversed between high and low.

13. (New) The method for driving a nonvolatile memory according to claim 12, wherein during read-out, a read-out voltage is across the ground terminal and the power source voltage terminal.